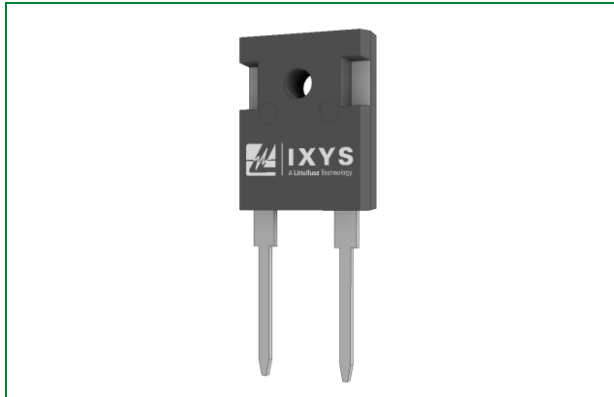


LSIC2SD170B25 1700 V, 25 A SiC Schottky Barrier Diode

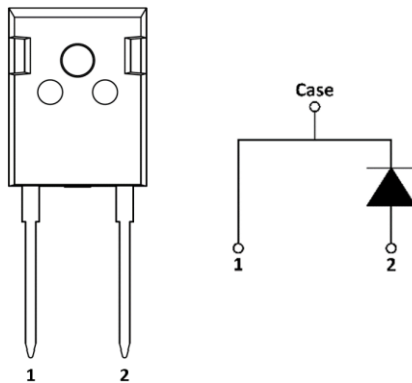


Agency Approvals and Environmental

Environmental Approvals



Pinout Diagram



Product Summary

Characteristic	Value	Unit
V_{RRM}	1700	V
$I_F (T_C \leq 135^\circ\text{C})$	34	A
$Q_C (V_R: 0-800\text{ V})$	175	nC

Features

- Positive temperature coefficient for safe operation and ease of paralleling
- 175 °C maximum operating junction temperature
- Excellent surge capability
- Extremely fast, temperature-independent switching behavior
- Dramatically reduced switching losses compared to Si bipolar diodes
- Zero reverse recovery current

Applications

- Boost diodes in PFC or DC/DC stages
- Switch-mode power supplies
- Solar inverters
- Uninterruptable power supplies
- Industrial motor drives
- Battery Chargers
- High speed rectifier

1. Maximum Ratings.....3

2. Thermal Characteristics3

3. Electrical Characteristics.....3

4. Performance Curves4

5. V_F Model for Simulation5

6. Package Dimensions6

7. Part Numbering and Marking.....7

8. Packing Options7

9. Packing Specifications7

1. Maximum Ratings

Characteristic	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	-	1700	V
DC Blocking Voltage	V_R	-	1700	V
Continuous Forward Current	I_F	$T_C = 25\text{ }^{\circ}\text{C}$	70	A
		$T_C = 135\text{ }^{\circ}\text{C}$	34	
		$T_C = 150\text{ }^{\circ}\text{C}$	25	
Non-repetitive Forward Surge Current	I_{FSM}	$T_C = 25\text{ }^{\circ}\text{C}$, $t_p = 10\text{ ms}$, Half sine pulse	144	A
I^2t	$\int I^2 dt$	$T_C = 25\text{ }^{\circ}\text{C}$, $t_p = 10\text{ ms}$, Half sine pulse	103	A^2s
Power Dissipation	P_{Tot}	$T_C = 25\text{ }^{\circ}\text{C}$	340	W
		$T_C = 110\text{ }^{\circ}\text{C}$	147	
Operating Junction Temperature	T_J	-	-55 to 175	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-	-55 to 150	$^{\circ}\text{C}$
Mounting Torque	M_D	M3 or 6-32 screw	0.6	Nm

2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance	$R_{thJC, max}$	0.44	$^{\circ}\text{C/W}$

3. Electrical Characteristics

Characteristic	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Forward Voltage	V_F	$I_F = 25\text{ A}$, $T_C = 25\text{ }^{\circ}\text{C}$	-	1.5	1.8	V
		$I_F = 25\text{ A}$, $T_C = 175\text{ }^{\circ}\text{C}$	-	2.2	-	
Reverse Current	I_R	$V_R = 1700\text{ V}$, $T_C = 25\text{ }^{\circ}\text{C}$	-	2	100	μA
		$V_R = 1700\text{ V}$, $T_C = 175\text{ }^{\circ}\text{C}$	-	50	-	
Total Capacitance	C	$V_R = 1\text{ V}$, $f = 1\text{ MHz}$	-	1860	-	pF
		$V_R = 400\text{ V}$, $f = 1\text{ MHz}$	-	167	-	
		$V_R = 800\text{ V}$, $f = 1\text{ MHz}$	-	120	-	
Total Capacitive Charge	Q_C	$V_R = 800\text{ V}$, $Q_C = \int Q(V) dV$	-	175	-	nC
Capacitive Stored Energy	E_C	$V_R = 800\text{ V}$	-	39	-	μJ

4. Performance Curves

Figure 1. Typical Forward Characteristics

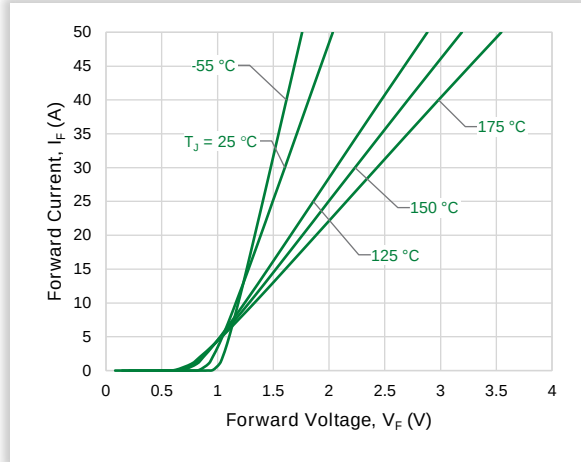


Figure 2. Typical Reverse Characteristics

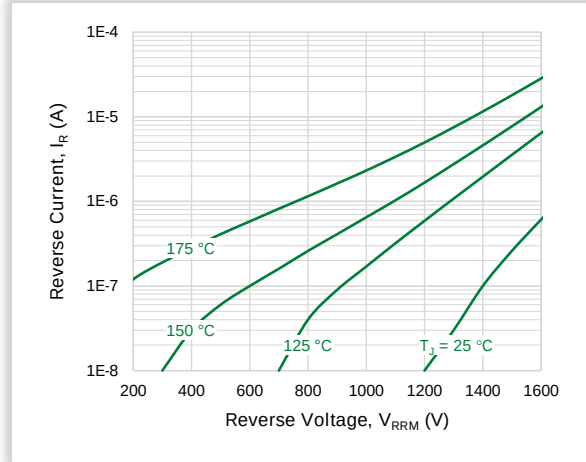


Figure 3. Power Derating

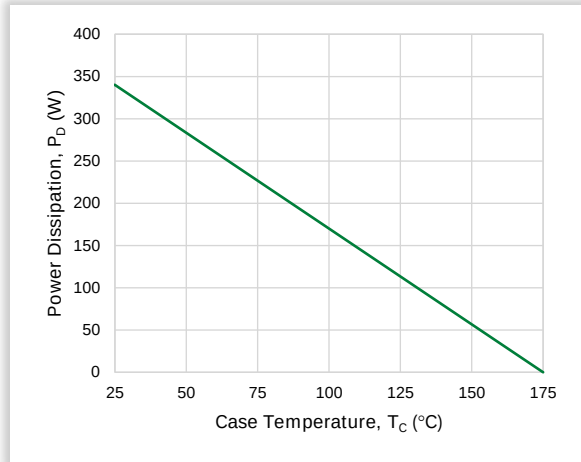


Figure 4. Current Derating

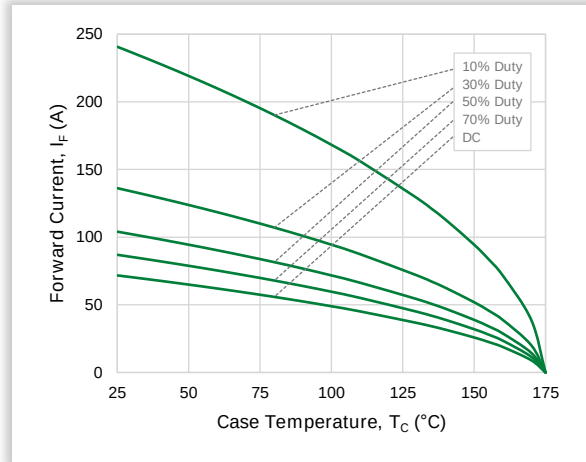


Figure 5. Capacitance vs. Reverse Voltage

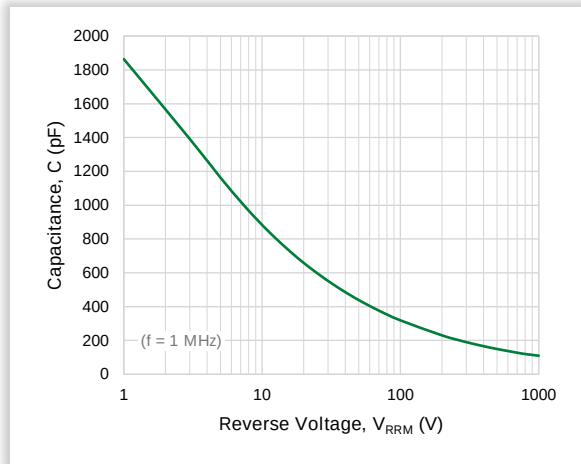


Figure 6. Capacitive Charge vs. Reverse Voltage

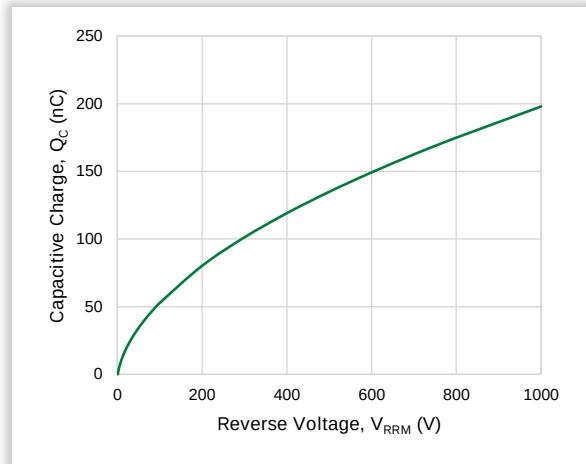


Figure 7. Stored Energy vs. Reverse Voltage

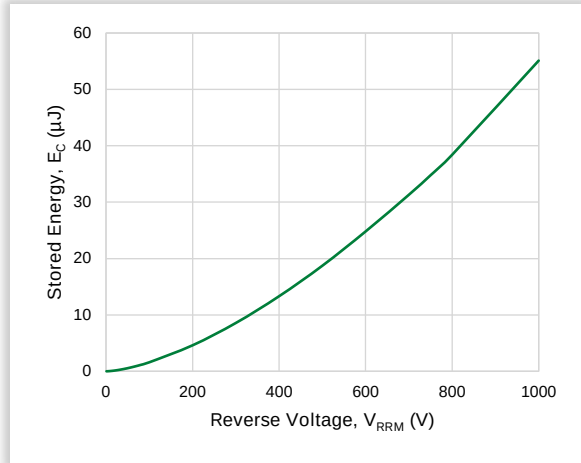
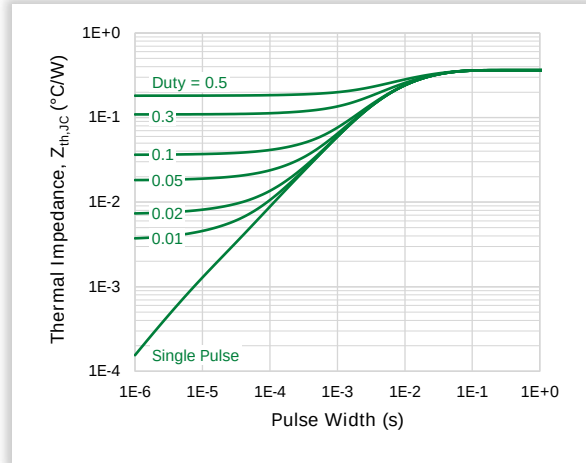
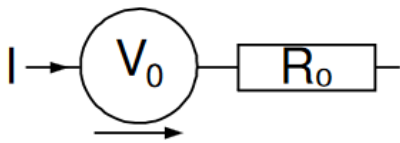


Figure 8. Transient Thermal Impedance



5. V_F Model for Simulation



$$V_F(T_J) = V_0 + IR_0$$

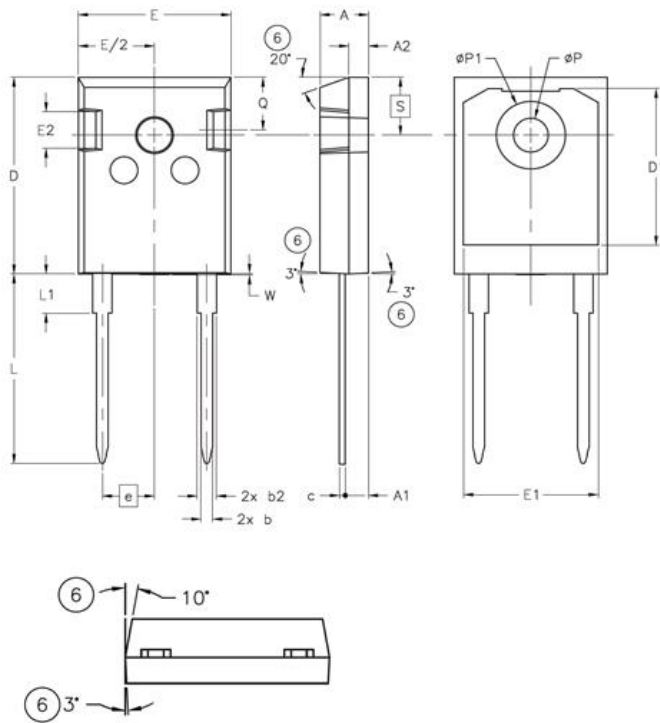
$$V_0 = -1.18 \times 10^{-3} \cdot T_J + 9.85 \times 10^{-1}$$

$$R_0 = 6.35 \times 10^{-7} \cdot T_J^2 + 9.72 \times 10^{-5} \cdot T_J + 1.88 \times 10^{-2}$$

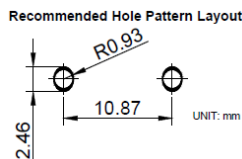
Notes:

- T_J is junction temperature in °C
- Range valid from 25 °C to 175 °C
- Model represents performance of a typical part

6. Package Dimensions



Recommended Hole Pattern Layout:

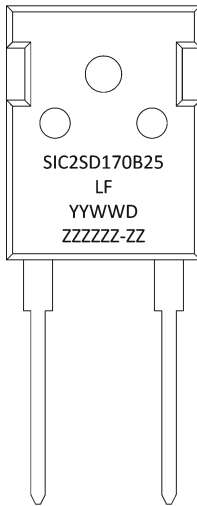


Notes:

1. Dimensions are in millimeters
2. Dimension D, E do not include mold flash. Mold flash shall not exceed 0.127 mm per side measured at outer most extreme of plastic body.
3. øP to have a maximum draft angle of 38.1 mm to the top of the part with a maximum hole diameter of 3.912 mm.

Symbol	Millimeters		
	Min	Nom	Max
A	4.7	-	5.31
A1	2.21	-	2.59
A2	1.5	-	2.49
b	0.99	-	1.4
b2	1.65	-	2.39
c	0.38	-	0.89
D	20.8	-	21.46
D1	13.08	-	-
D2	0.51	-	1.35
e	5.44 BSC		
E	15.49	-	16.26
E1	13.46	-	-
E2	3.43	-	3.99
L	19.81	-	20.32
L1	-	-	4.5
øP	3.56	-	3.66
øP1	7.06	-	7.39
Q	5.38	-	6.2
S	6.17 BSC		
W	-	-	0.15

7. Part Numbering and Marking

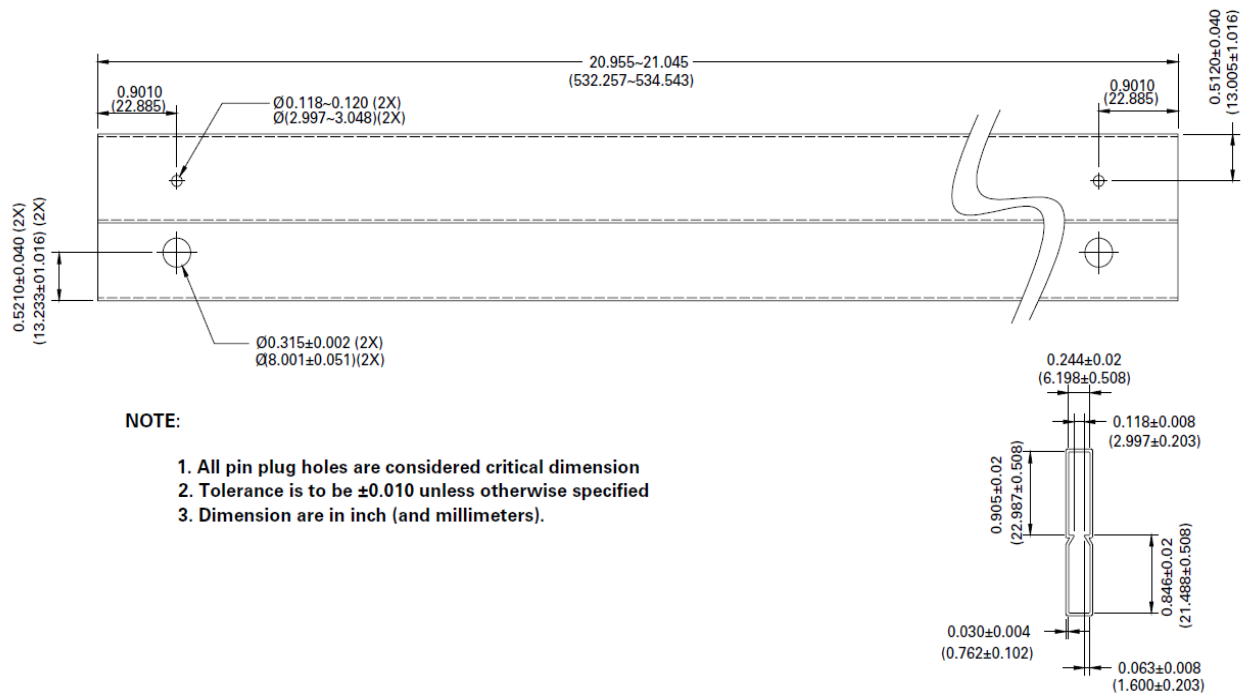


SiC	= SiC
2	= Gen 2
SD	= Schottky Barrier Diode
170	= Voltage Rating (1700 V)
B	= Package (TO-247-2L)
25	= Current Rating (25 A)
YY	= Year
WW	= Week
D	= Special Code
ZZZZZZ-ZZ	= Lot Number

8. Packing Options

Part Number	Marking	Packing Mode	M.O.Q.
LSIC2SD170B25	SIC2SD170B25	Tube (30 pcs)	30 pcs

9. Packing Specifications



For additional information please visit www.Littelfuse.com/powersemi

Disclaimer Notice - Littelfuse products are not designed for, and shall not be used for, any purpose (including, without limitation, automotive, military, aerospace, medical, life-saving, life-sustaining or nuclear facility applications, devices intended for surgical implant into the body, or any other application in which the failure or lack of desired operation of the product may result in personal injury, death, or property damage) other than those expressly forth in applicable Littelfuse product documentation. Littelfuse shall not be liable for any claims or damages arising out of products used in applications not expressly intended by Littelfuse as set forth in applicable Littelfuse documentation.

Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics